OK TO ENTER: /JSR/

METHOD OF FORMING STORAGE NODES IN A DRAM

Appl. No.	: 09/851,580	Confirmation No. 3189
Applicant	: Jiunn-Ren Hwang et al.	
Filed	: May 10, 2001	
TC/A.U.	: 1795	
Examiner	: Ruggles, John S	
Docket No.	: NAUP0292USA	
Customer No.	: 27765	

Commissioner for Patents
P.O. Box 1450
Alexandria VA 22313-1450

AMENDMENT

5   Sir:

   In response to the Office action of October 21, 2008, please amend the
above-identified application as follows:

Listing of the Claims begins on page 2 of this paper.

Amendments to the Drawings begin on page 3 of this paper.

10   **Remarks/Arguments** begin on page 4 of this paper.

An **Appendix** including amended drawing figures is attached following
page 5 of this paper.